Revision. 2

MOS FET

MTM684110LBF

Panasonic

MTM684110LBF

Dual P-channel MOSFET

For switching

■ Features

- Low drain-source On-state Resistance RDS(on) typ. = 23 mΩ (VGS =-5.0 V)
- Low drive voltage:1.8V drive
- Halogen-free / RoHS compliant (EU RoHS / UL-94 V-0 / MSL:Level 1 compliant)
- Marking Symbol 1D
- Basic Part Number: Dual MTM76111 (Individual)

■ Packaging

Established: 2011-03-25

: 2013-10-15

Revised

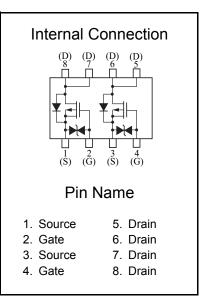
Embossed type (Thermo-compression sealing) 3 000 pcs / reel (standard)

■ Absolute Maximum Ratings Ta = 25 °C

Parameter		Symbol	Rating	Unit	
	Drain-source Voltage	VDS	-12	V	
	Gate-source Voltage	VGS	±8	V	
	Drain current	ID	-4.8	Α	
	Peak drain current	IDp	-19	Α	
Overall	Total power dissipation *1	PD	1.0	W	
	Channel temperature	Tch	150	°C	
	Operating ambient temperature	Topr	-40 to +85	°C	
	Storage temperature	Tstg	-55 to +150	°C	

Note) *1 Glass epoxy board: 25.4 mm × 25.4 mm × 0.8 mm Copper foil of the drain portion should have a area of 300 mm² or more PD absolute maximum rating without a heat shink: 400 mW

Unit: mm 0.16 (0.81)0.65 1. Source 5. Drain 6. Drain 2. Gate 3. Source 7. Drain 4. Gate 8. Drain Panasonic WMini8-F1 JEITA SC-115 Code



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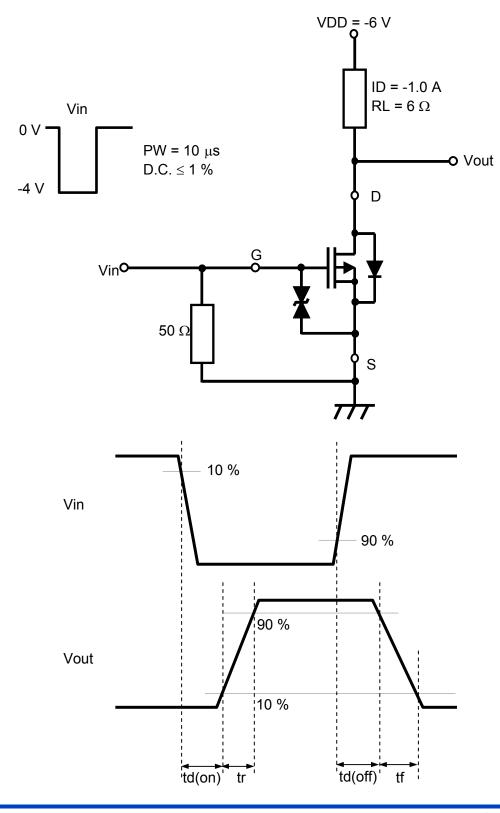
■ Electrical Characteristics Ta = 25°C ± 3°C

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Drain-source surrender voltage	VDSS	ID = -1 mA, VGS = 0	-12			V
Drain-source cutoff current	IDSS	VDS = -10 V, VGS = 0			-0.1	μA
Gate-source cutoff current	IGSS	$VGS = \pm 8 \text{ V}, VDS = 0$			±10	μA
Gate threshold voltage	Vth	ID = -1.0 mA, VDS = -6.0 V	-0.3	-0.65	-1.0	V
	RDS(ON)1	ID = -1.0 A, VGS = -5.0 V		23	32	mΩ
Drain-source ON resistance	RDS(ON)2	ID = -0.5 A, VGS = -2.5 V		27	40	mΩ
	RDS(ON)3	ID = -0.2 A, VGS = -1.8 V		36	60	mΩ
Forward transfer admittance	Yfs	ID = -1.0 A, VDS = -10 V	3.5			S
Short-circuit input capacitance (Common source)	Ciss			1400		pF
Short-circuit output capacitance (Common source)	Coss	VDS = -10 V, VGS = 0, f = 1 MHz		135		pF
Reverse transfer capacitance (Common source)	Crss			150		pF
Turn-on delay time *1	td(on)	VDD = -6 V, VGS = 0 V to -4 V		9		ns
Rise time *1	tr	ID = -1.0 A		11		ns
Turn-off delay time *1	td(off)	VDD = -6 V, VGS = -4 V to 0 V		270		ns
Fall time *1	tf	ID = -1.0 A	·	160	·	ns

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 Measuring methods for transistors.

^{2. *1} Measurement circuit for Turn-on Delay Time/Rise Time/Turn-off Delay Time/Fall Time

*2 Measurement circuit for Turn-on Delay Time/Rise Time/Turn-off Delay Time/Fall Time

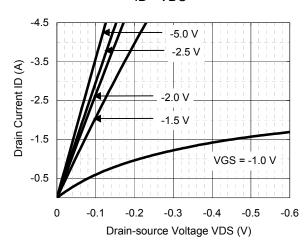


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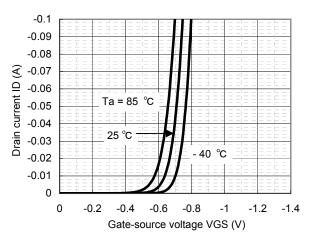
MOS FET MTM684110LBF

Technical Data (reference)

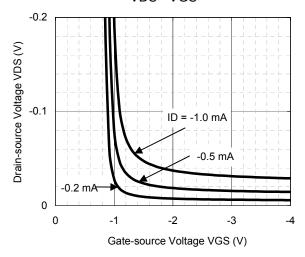
ID - VDS



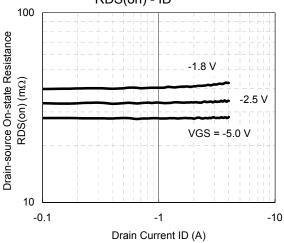
ID - VGS



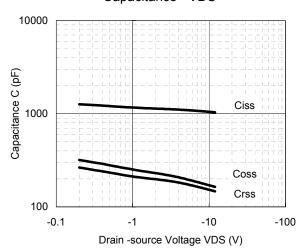
VDS - VGS



RDS(on) - ID



Capacitance - VDS



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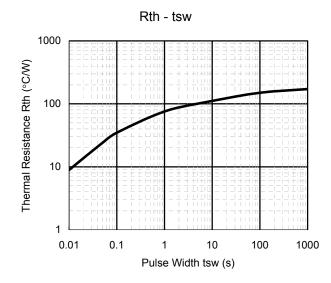
Established: 2011-03-25 Revised

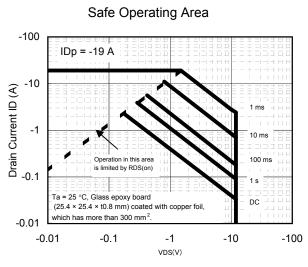
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Technical Data (reference)

Vth - Ta RDS(on) - Ta -1 60 Gate-source Threshold Voltage Vth (V) Drain-source On-resistance VGS = - 1.8 V 50 (GM) (MQ) 30 20 -0.5 - 5.0 V 10 0 -0 0 50 100 150 -50 -50 50 100 150 Temperature (°C) Temperature (°C)

PD - Ta 1.2 Mounted on glass epoxy board Total Power Dissipation PD (W) $(25.4 \times 25.4 \times 0.8 \text{ mm})$ coated with copper foil,which has more 1 than 300 mm². 0.8 0.6 Non-heat sink 0.4 0.2 0 0 50 100 150 Temperature Ta (°C)





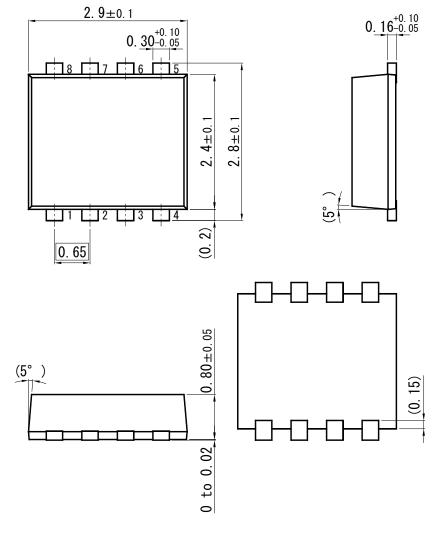
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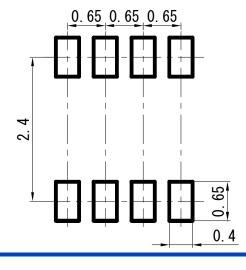
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WMini8-F1

Unit: mm



■ Land Pattern (Reference) (Unit: mm)



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